

10/565624

IP20 Rec'd PCT/PTO 24 JAN 2006

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re U.S. Patent Application of )  
SUDA et al. )  
Application Number: To Be Assigned )  
Filed: Concurrently Herewith )  
For: FIELD EFFECT TRANSISTOR AND METHOD FOR )  
MANUFACTURING SAME )  
ATTORNEY DOCKET NO. HIRA.0217 )

Honorable Assistant Commissioner  
for Patents  
Washington, D.C. 20231

**INFORMATION DISCLOSURE STATEMENT**

Pursuant to 37 C.F.R. §§ 1.56 and 1.97, this Information Disclosure Statement is submitted in the above-identified National Stage U.S. patent application. A listing of documents to be published on the face of any patent granted from this application is submitted herewith on Form PTO-1449. Any other documents or information submitted for consideration by the Examiner are listed in this paper. A copy of each foreign patent, or each publication or portion thereof listed or herein identified, is submitted herewith.

**CERTIFICATION**

This Information Disclosure Statement is submitted with the initial filing of the application. Accordingly, no fee is due or payable at this time.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

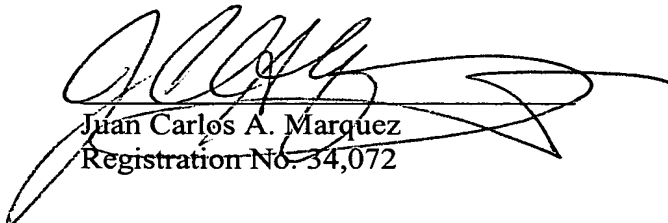
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Please charge any additional fees or credit any overpayments in connection with this paper to Deposit Account No. 08-1480.

Respectfully submitted,

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Form PTO 1449  U.S. Department of Commerce Patent and Trademark Office  Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER HIRA.0217	SERIAL NUMBER To be Assigned <b>10/565.624</b>
	APPLICANT SUDA et al.	
	FILING DATE Concurrently Herewith	GROUP

## U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
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## Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
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EXAMINER	DATE CONSIDERED
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PTO1449